

Silicon Epitaxial Planar Diode

BAV21WS

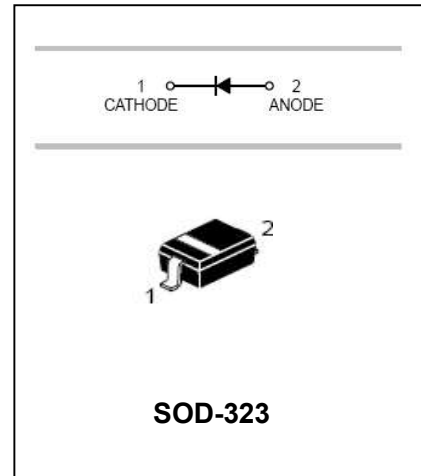
FEATURES

- Fast Switching Speed.
- Surface Mount Package Ideally Suited For Automatic Insertion.
- For General Purpose Switching Applications.
- High Conductance.



Lead-free

HF



APPLICATIONS

- Surface mount fast switching diode.

ORDERING INFORMATION

Type No.	Marking	Package Code
BAV21WS□	T3	SOD-323

- : none is for Lead Free package;
“G” is for Halogen Free package.

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	BAV21WS	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	250	V
Working Peak Reverse Voltage	V_{RWM}	200	V
DC Reverse Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	141	V
Average Rectified Output Current	I_o	200	mA
Non-Repetitive Peak Forward Surge Current @t=1.0 ms @t=1.0 s	I_{FSM}	2.5	A
		0.5	
Repetitive Peak Forward Surge Current	I_{FRM}	625	mA
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	625	°C/W
Thermal Resistance Junction to Case	$R_{\theta JC}$	250	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

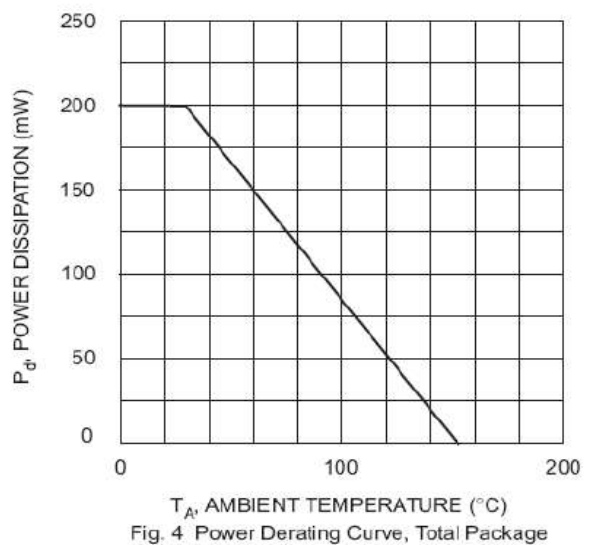
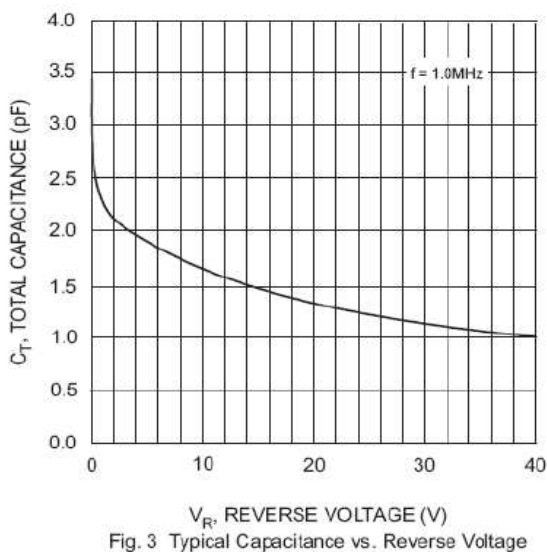
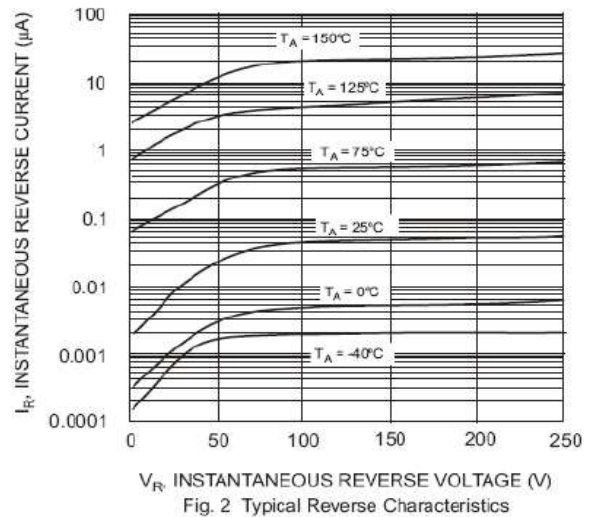
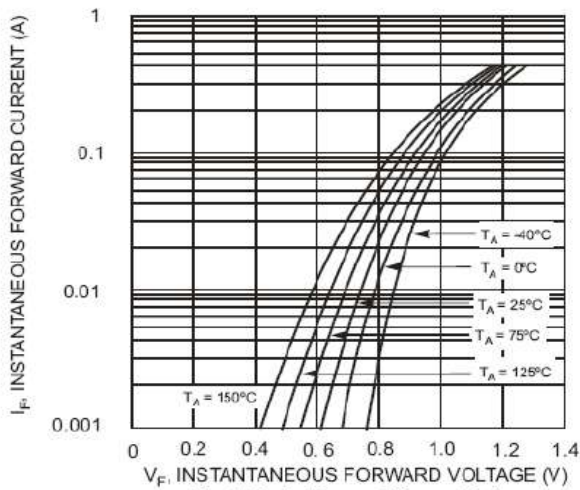
Silicon Epitaxial Planar Diode

BAV21WS

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Test Condition	Min	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R=100\mu A$	250	-	V
Forward Voltage	V_{FM}	$I_F=100mA$ $I_F=200mA$	-	1.0 1.25	V
Reverse Current	I_R	$V_R=200V$ $V_R=200V, T_J=125^\circ C$	-	0.1 20	μA
Capacitance between terminals	C_T	$V_R=0, f=1.0MHz$	-	5	pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=30mA,$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$	-	50	ns

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



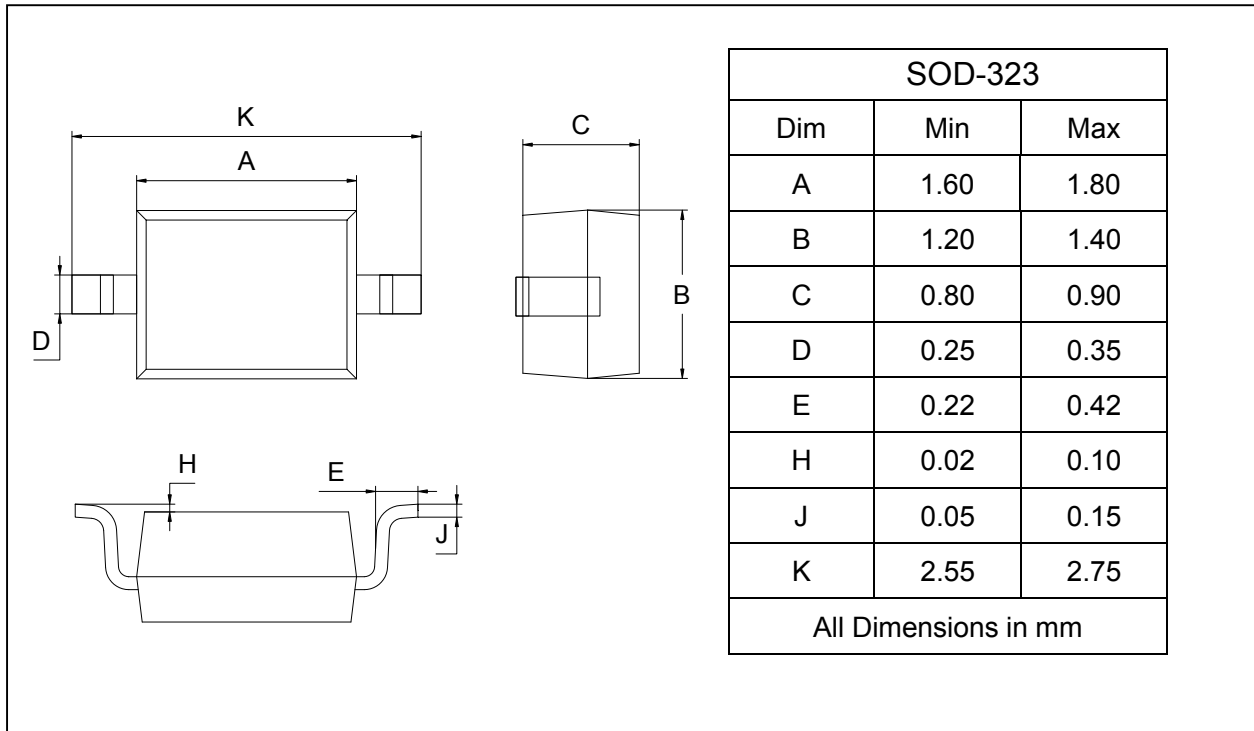
Silicon Epitaxial Planar Diode

BAV21WS

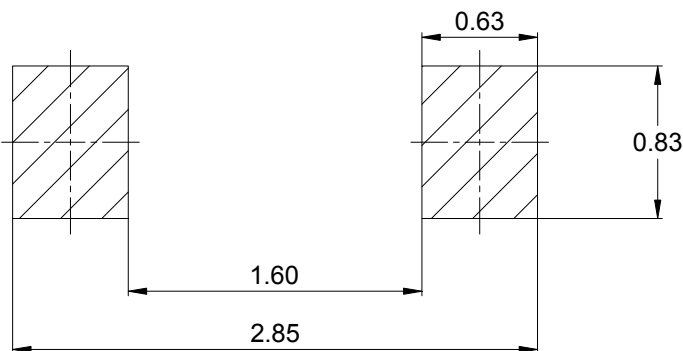
PACKAGE OUTLINE

Plastic surface mounted package

SOD-323



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
BAV21WS	SOD-323	3000/Tape&Reel